

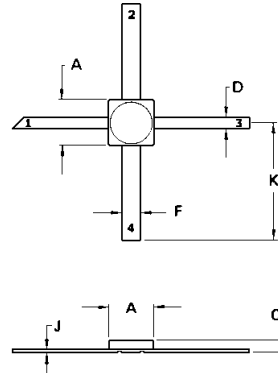
# SILICON NPN RF TRANSISTOR

**DESCRIPTION:**

The **MRF572** is Designed for Low Noise General Purpose VHF,UHF Amplifier and Oscillator Applications.

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	60 mA
<b>V<sub>CE</sub></b>	12 V
<b>P<sub>DISS</sub></b>	500 mW @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C

**PACKAGE STYLE 100MIL CERAMIC STRIPLINE**


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
<b>A</b>	2.29	2.67	0.090	0.105
<b>C</b>	0.89	1.40	0.035	0.055
<b>D</b>	0.41	0.61	0.016	0.024
<b>F</b>	0.89	1.09	0.035	0.043
<b>J</b>	0.08	0.15	0.003	0.006
<b>K</b>	4.45	5.84	0.175	0.230

1 = Collector    2 & 4 = Emitter  
3 = Base

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 1.0 mA			12			V
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 μA			20			V
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 8.0 V					200	μA
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 50 μA			1.5			V
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 10 mA		30		300	---
<b>C<sub>cb</sub></b>	V <sub>CB</sub> = 8.0 V		f = 1.0 MHz		0.25		pF
<b>f<sub>t</sub></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 25 mA	f = 1.0 GHz		8.0		GHz
<b> S<sub>21E</sub> <sup>2</sup></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 25 mA	f = 1.0 GHz f = 2.0 GHz		16.9 12.0		dB
<b>GNF</b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 0 mA	f = 0.5 GHz f = 1.0 GHz f = 2.0 GHz	10	16.5 12		dB
<b>NF</b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 0 mA	f = 0.5 GHz f = 1.0 GHz f = 2.0 GHz		1.0 1.5 2.5	2.0	dB